



TPS7A6650H-Q1 40V、超低 $I_{(q)}$ 、环境温度最高为 150°C 的稳压器

1 特性

- 适用于汽车电子 应用
- 具有符合 AEC-Q100 标准的下列结果：
 - 器件温度：-40°C 至 150°C 的环境工作温度范围
 - 器件人体模型 (HBM) 静电放电 (ESD) 分类等级 H2
 - 器件组件充电模式 (CDM) ESD 分类等级 C4
- 4V 至 40V 的宽输入电压范围，瞬态电压高达 45V
- 输出电流：50mA
- 低静态电流 ($I_{(q)}$):
 - 当 EN = 低电平时（关断模式）时为 2μA
 - 轻负载时典型值为 12μA
- 低等效串联电阻 (ESR) 陶瓷输出稳定电容器 (2.2μF-100μF)
- 50mA 时的压降电压为 130mV
($V_{(vin)}$ = 4V 时的典型值)
- 5V 固定输出电压
- 低输入电压跟踪
- 集成型加电复位
 - 可编程复位脉冲延迟
 - 漏极开路复位输出
- 集成故障保护
 - 热关断
 - 短路保护功能
- 8 引脚 MSOP-DGN 封装

2 应用

- 动力传动传感器模块
- 具有睡眠模式的信息娱乐系统
- 车身控制模块
- 常开电池 应用
 - 网关 应用
 - 遥控无钥匙进入系统
 - 发动机防盗锁止系统

3 说明

TPS7A6650H-Q1 是一款低压降线性稳压器，其设计适用于输入电压高达 40V 的操作。该器件在无负载时的静态电流仅为 12μA，非常适合待机微处理器控制单元系统，尤其是汽车 应用。

该器件 具有 集成式短路和过流保护。此器件在上电时执行复位延迟以指示输出电压稳定且处于稳压状态。用户可使用一个外部电容器来设定此延迟。低压跟踪特性允许使用更小的输入电容器并且有可能在冷启动条件下无需使用升压转换器。

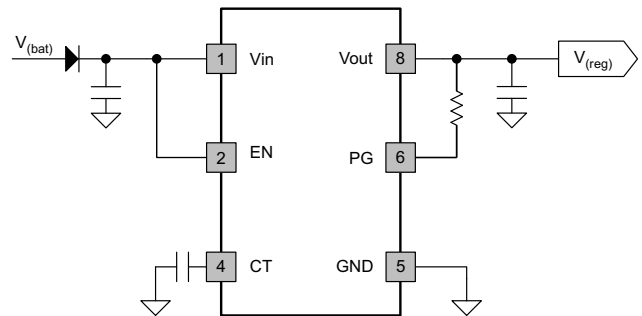
该器件可在 -40°C 至 150°C 的温度范围内工作，非常适合各类汽车应用中的 电源。

器件信息(1)

器件型号	封装	封装尺寸（标称值）
TPS7A6650H-Q1	HVSSOP (8)	3.00mm x 3.00mm

(1) 如需了解所有可用封装，请见数据表末尾的可订购产品附录。

硬件使能选项



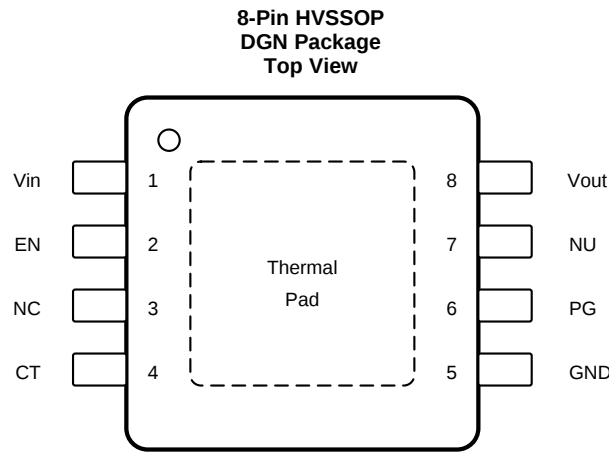
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4 修订历史记录

日期	修订版本	注释
2015 年 11 月	*	最初发布版本

5 Pin Configuration and Functions



NC – No internal connection

NU – Make no external connection

Pin Functions

PIN NAME	PIN NO.	TYPE	DESCRIPTION
CT	4	O	Reset-pulse delay adjustment. Connect this pin via a capacitor to GND
EN	2	I	Enable pin. The device enters the standby state when the enable pin becomes lower than the threshold.
NU	7	I	Not-used pin; make no external connection
GND	5	G	Ground reference
NC	3	—	Not-connected pin
PG	6	O	Output ready. This open-drain pin must connect to Vout via an external resistor. The output voltage going below threshold pulls it down.
Vin	1	P	Input power-supply voltage
Vout	8	O	Output voltage
—	—	—	Thermal pad

6 Specifications

6.1 Absolute Maximum Ratings

over operating ambient temperature range (unless otherwise noted) ⁽¹⁾

		MIN	MAX	UNIT
Vin, EN	Unregulated input ⁽²⁾ ⁽³⁾	−0.3	45	V
Vout	Regulated output	−0.3	7	V
CT		−0.3	25	V
PG		−0.3	Vout	V
T _J	Operating junction temperature range	−40	160	°C
T _{stg}	Storage temperature range	−65	160	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values are with respect to GND

(3) Absolute maximum voltage, withstand 45 V for 200 ms

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 ⁽¹⁾	±4000	V
		Charged device model (CDM), per AEC Q100-011	All pins ±1000	
			Corner pins (1, 4, 5, and 8) ±1000	

(1) AEC Q100-002 indicates HBM stressing is done in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

over operating ambient temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V _{in}	Unregulated input	4	40	V
EN		0	40	V
CT		0	20	V
V _{out}		1.5	5.5	V
PG	Low voltage (I/O)	0	5.5	V
T _A	Operating ambient temperature	–40	150	°C

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TPS7A6650H-Q1	UNIT
		DGN (HVSSOP)	
		8 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	63.4	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	53	°C/W
R _{θJB}	Junction-to-board thermal resistance ⁽²⁾	37.4	°C/W
ψ _{JT}	Junction-to-top characterization parameter	3.7	°C/W
ψ _{JB}	Junction-to-board characterization parameter	37.1	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	13.5	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report ([SPRA953](#)).

(2) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.

6.5 Electrical Characteristics

V_(Vin) = 14 V, 1 mΩ < ESR < 2 Ω, T_J = –40°C to 160°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY VOLTAGE AND CURRENT (V_{in})					
V _(Vin)	Input voltage	I _O = 1 mA	5.5	40	V
I _(q)	Quiescent current	V _(Vin) = 5.5 V to 40 V, EN = ON, I _O = 0.2 mA	12	22	μA
I _(Sleep)	Input sleep current	No load current and EN = OFF		4	μA
I _(EN)	EN pin current	V _(EN) = 40 V		1	μA
V _(VinUVLO)	Undervoltage detection	Ramp V _(Vin) down until output turns OFF		2.6	V
V _(UVLOhys)	Undervoltage hysteresis		1		V
ENABLE INPUT (EN)					
V _{IL}	Logic input low level		0	0.4	V
V _{IH}	Logic input high level		1.7		V

Electrical Characteristics (接下页)

 $V_{(Vin)} = 14\text{ V}$, $1\text{ m}\Omega < \text{ESR} < 2\text{ }\Omega$, $T_J = -40^\circ\text{C}$ to 160°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
REGULATED OUTPUT (Vout)						
V(Vout)	Regulated output	I _O = 1 mA, T _J = 25°C	-1%		1%	
		V(Vin) = 6 V to 40 V, I _O = 1 mA to 50 mA	-2%		2%	
V(line-reg)	Line regulation	V(Vin) = 5.5 V to 40 V, I _O = 50 mA			5	mV
V(load-reg)	Load regulation	I _O = 1 mA to 50 mA			20	mV
V(dropout)	Dropout voltage	V(dropout) = V(Vin) – V(Vout), I _{OUT} = 50 mA		130	240	mV
I _O	Output current	V(Vout) in regulation	0		50	mA
I(lreg-CL)	Output current limit	V(Vout) short to ground		500	800	mA
PSRR	Power supply ripple rejection ⁽¹⁾	V(Vin) = 12 V, I _L = 10 mA, output capacitance = 2.2 μF,				
		V(Vin) = 12 V, I _L = 10 mA, output capacitance = 2.2 μF, frequency = 100 Hz		60		dB
		V(Vin) = 12 V, I _L = 10 mA, output capacitance = 2.2 μF, frequency = 100 kHz		40		dB
RESET (PG)						
V _{OL}	Reset output, low voltage	I _{OL} = 0.5 mA			0.4	V
I _{lkg}	Leakage current	Reset pulled Vout through 10-kΩ resistor			1	μA
V _(TH-POR)	Power-on-reset threshold	V(Vout) increasing	89.6	91.6	93.6	% of Vout
V _(Thres)	Hysteresis			2		% of Vout
RESET DELAY (CT)						
I _(Chg)	Delay-capacitor charging current	V _(CT) = 0 V		1.4		μA
V _(th)	Threshold to release PG high			1		V
OPERATING TEMPERATURE RANGE						
T _J	Junction temperature		-40		160	°C
T _(shutdown)	Junction shutdown temperature			175		°C
T _(hyst)	Hysteresis of thermal shutdown			20		°C

(1) Design information – Not tested

6.6 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
TIMING FOR RESET (PG)						
$t_{(POR)}$	Power-on-reset delay	Where C = delay capacitor value; capacitance C = 100 nF ⁽¹⁾	50	100	180	ms
$t_{(POR-fixed)}$		No capacitor on pin	100	290	650	μs
$t_{(Deglitch)}$	Reset deglitch time		20	250		μs

(1) This information only is not tested in production and equation basis is $(C \times 1) / 1 \times 10^{-6} = t_d$ (delay time).
Where C = Delay capacitor value. Capacitance C range = 100 pF to 100 nF .

6.7 Qualification Summary

The TPS7A6650H-Q1 device has passed all the Grade 0 level qualification items required in AEC-Q100 with one exception: High temperature storage lifetime (HTSL). For the HTSL item, the Grade 0 level requirement is passing 175°C for 1000 hours of stress. For this device, it passed at 160°C for 1000 hours stress.

6.8 Typical Characteristics

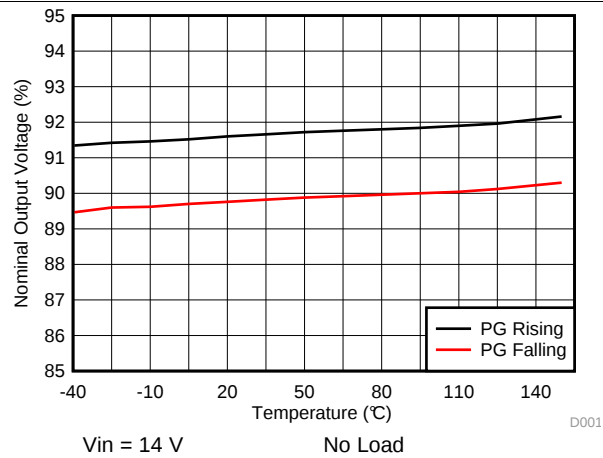


图 1. Power-Good Threshold Voltage vs Temperature

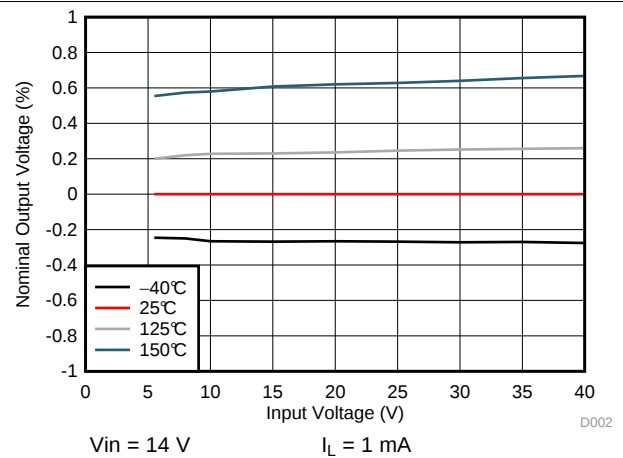


图 2. Line Regulation

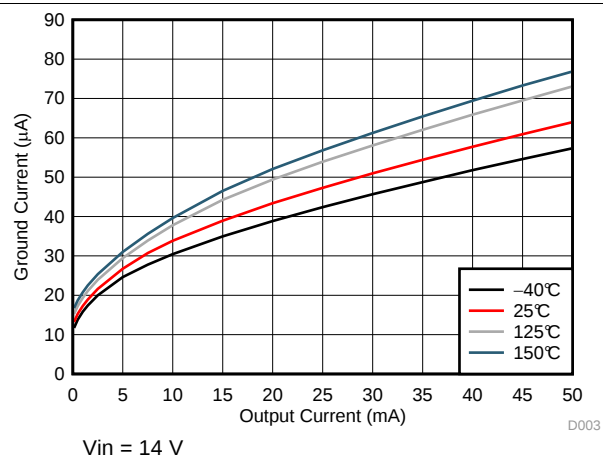


图 3. Ground Current vs Output Current

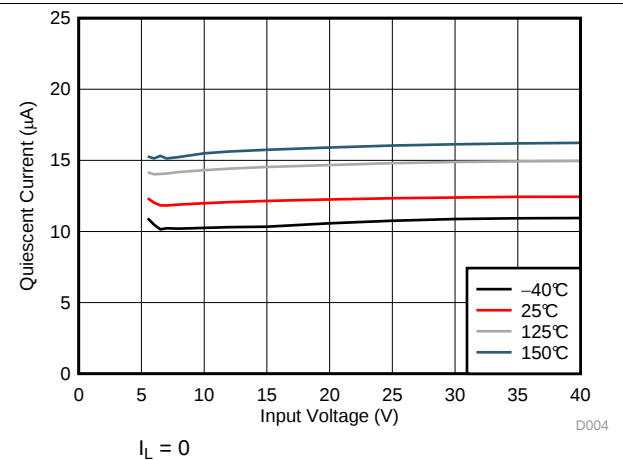


图 4. Quiescent Current vs Input Voltage

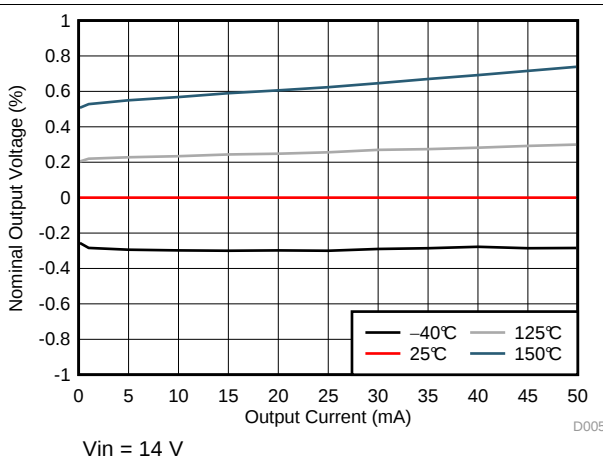


图 5. Load Regulation

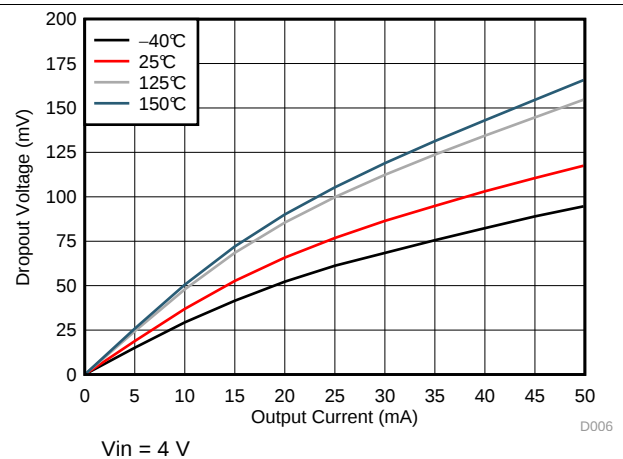


图 6. Dropout Voltage vs Output Current

Typical Characteristics (接下页)

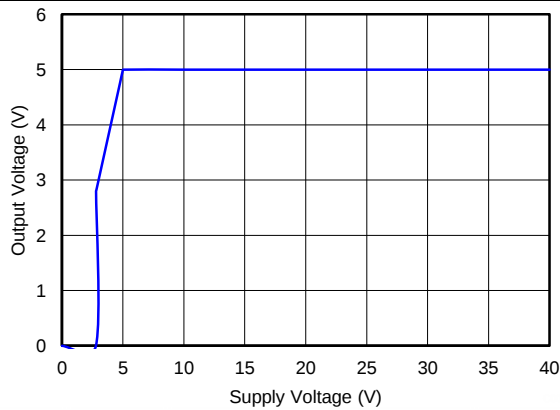


图 7. Output Voltage vs Supply Voltage (Fixed 5-V Version, $I_L = 0$)

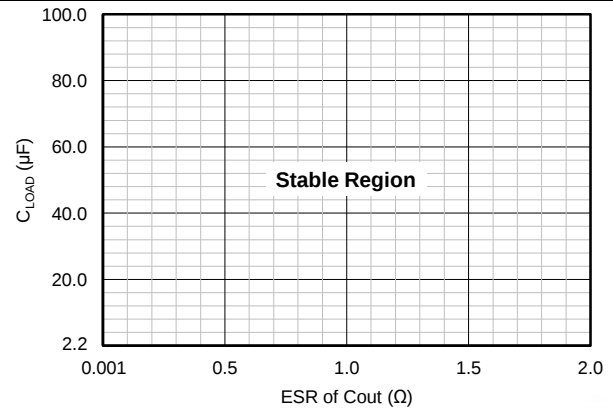


图 8. Load Capacitance vs ESR Stability

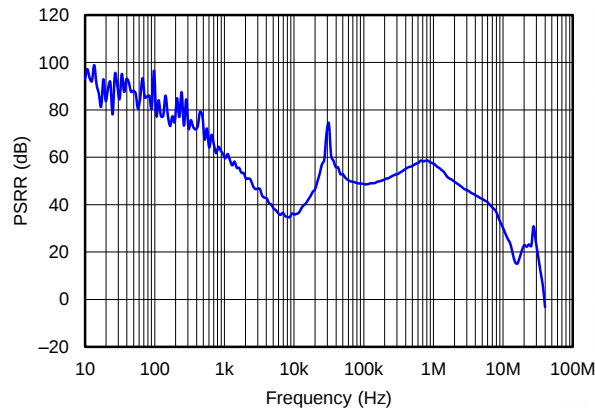


图 9. Power-Supply Rejection Ratio vs Frequency

All oscilloscope waveforms were taken at room temperature.

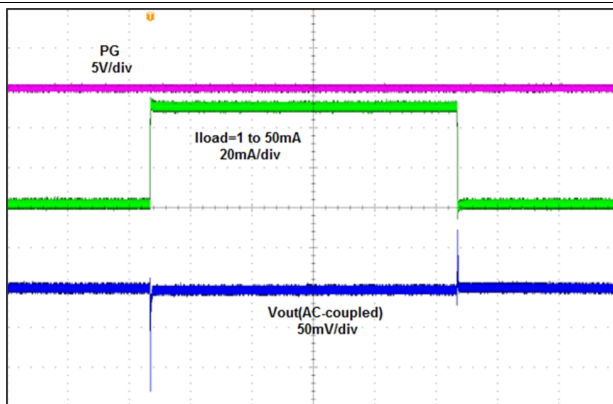


图 10. Load Transient Response, 10 ms/div

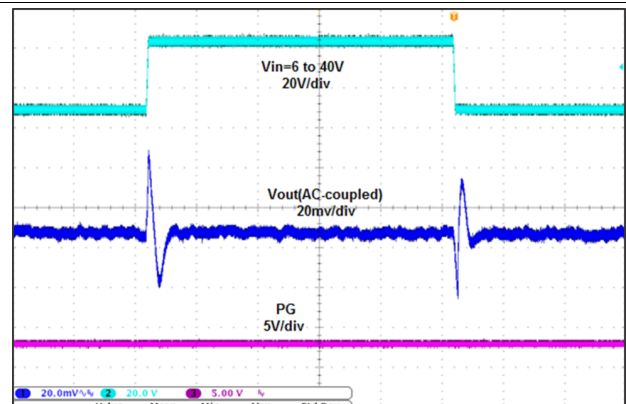


图 11. Line Transient Response, $I_L = 1$ mA, 1 V/ μ s

Typical Characteristics (接下页)

All oscilloscope waveforms were taken at room temperature.

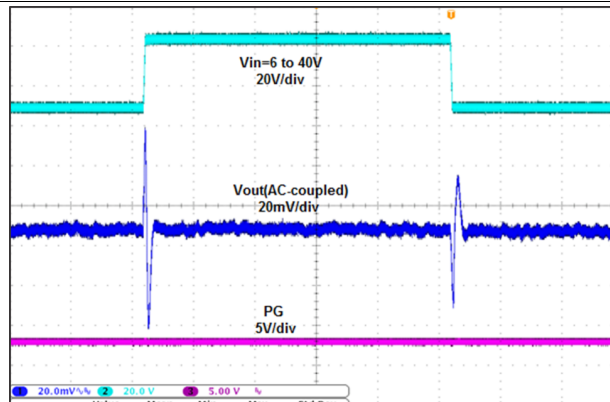


图 12. Line Transient Response, $I_L = 10 \text{ mA}$, $1 \text{ V}/\mu\text{s}$

7 Detailed Description

7.1 Overview

This product is a combination of a low-dropout linear regulator with reset function. The power-on reset initializes once the Vout output exceeds 91.6% of the target value. The power-on-reset delay is a function of the value set by an external capacitor on the CT pin before releasing the PG pin high.

7.2 Functional Block Diagram

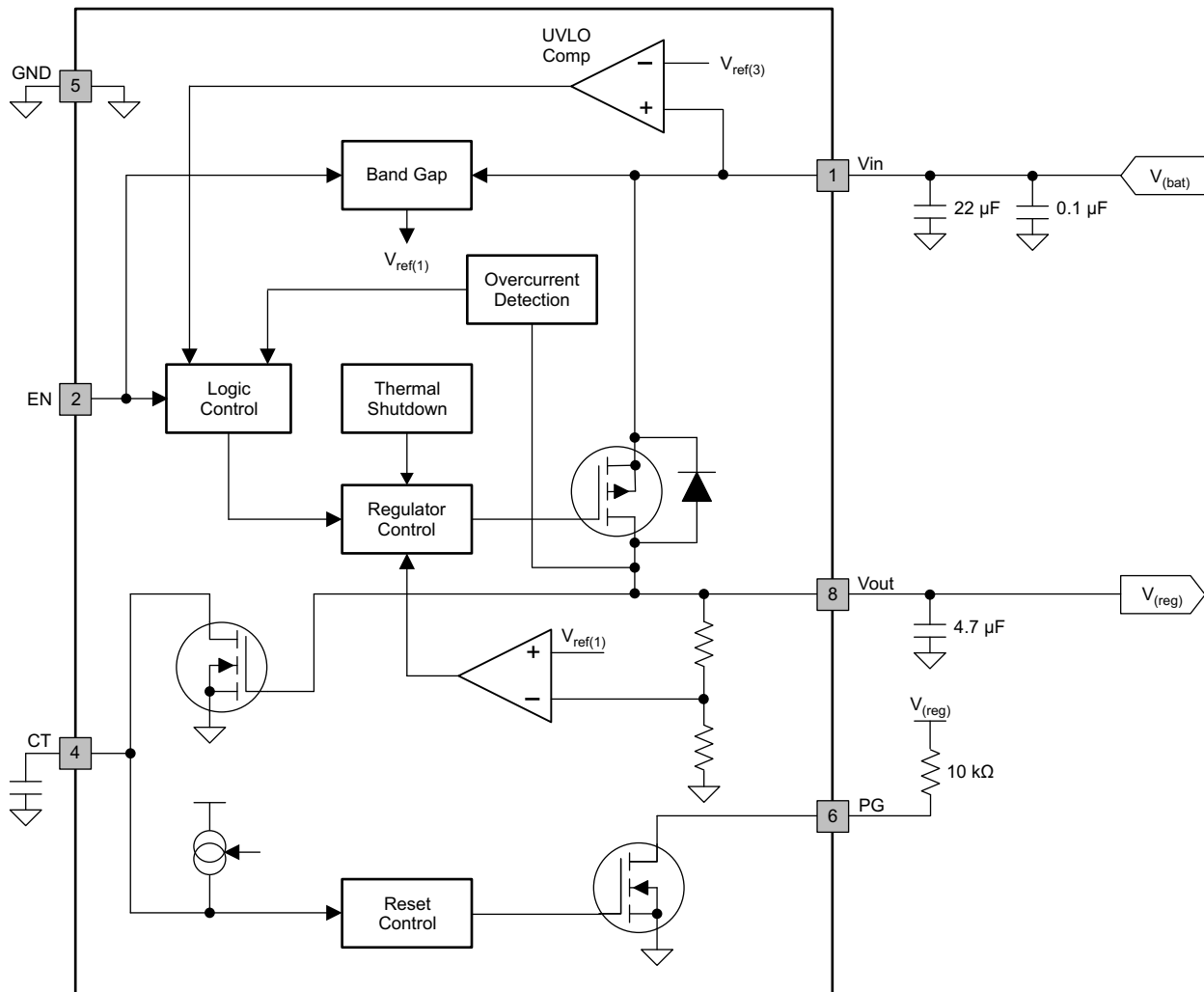


图 13. TPS7A6650H-Q1 Functional Block Diagram

7.3 Feature Description

7.3.1 Enable (EN)

This is a high-voltage-tolerant pin; high input activates the device and turns the regulator ON. One can connect this input to the Vin pin for self-bias applications.

7.3.2 Regulated Output (Vout)

This is the regulated output based on the required voltage. The output has current limitation. During initial power up, the regulator has a soft start incorporated to control initial current through the pass element and the output capacitor.

Feature Description (接下页)

In the event the regulator drops out of regulation, the output tracks the input minus a drop based on the load current. When the input voltage drops below the UVLO threshold, the regulator shuts down until the input voltage recovers above the minimum start-up level.

7.3.3 Power-On Reset (PG)

This is an output with an external pullup resistor to the regulated supply. The output remains low until the regulated V_{out} has exceeded approximately 90% of the set value and the power-on-reset delay has expired. The on-chip oscillator presets the delay. The regulated output falling below the 90% level asserts this output low after a short de-glitch time of approximately 250 μs (typical).

7.3.4 Reset Delay Timer (CT)

An external capacitor on this pin sets the timer delay before the reset pin is asserted high. The constant output current charges an external capacitor until the voltage exceeds a threshold to trip an internal comparator. If this pin is open, the default delay time is 290 μs (typ). After releasing the PG pin high, the capacitor on this pin discharges, thus allowing the capacitor to charge from approximately 0.2 V for the next power-on-reset delay-timer function.

An external capacitor, CT, defines the reset-pulse delay time, $t_{(POR)}$, with the charge time of:

$$t_{(POR)} = \frac{C_{(CT)} \times 1 V}{1 \mu A} \quad (1)$$

The power-on reset initializes once the output $V_{(Vout)}$ exceeds 91.6% of the programmed value. The power-on-reset delay is a function of the value set by an external capacitor on the CT pin before the releasing of the PG pin high.

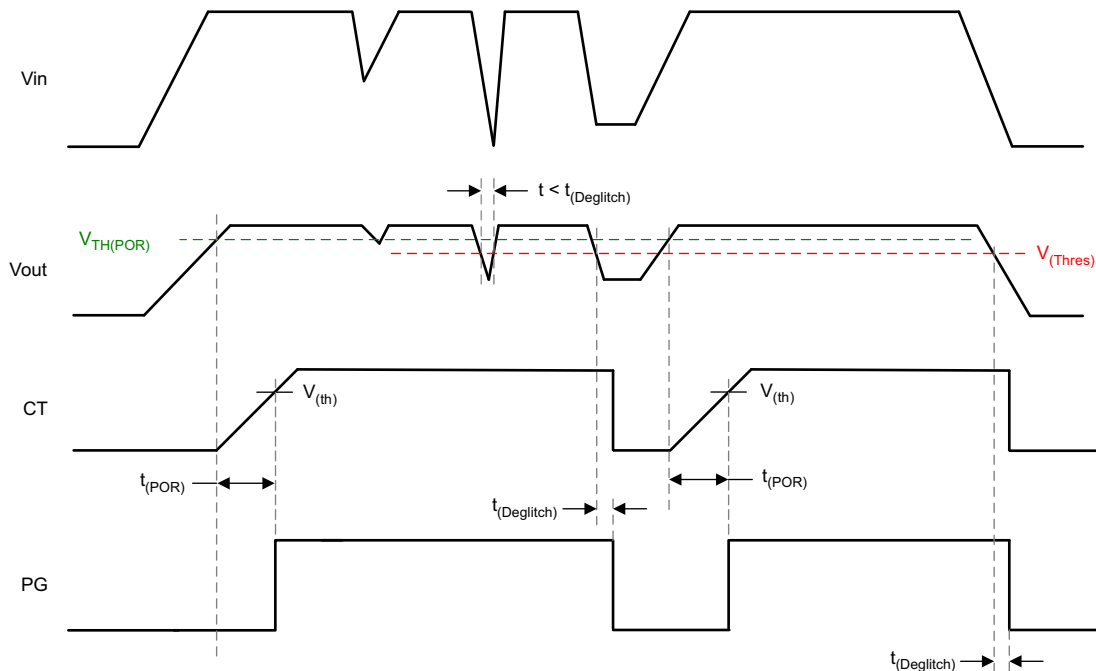


图 14. Conditions for Activation of Reset

Feature Description (接下页)

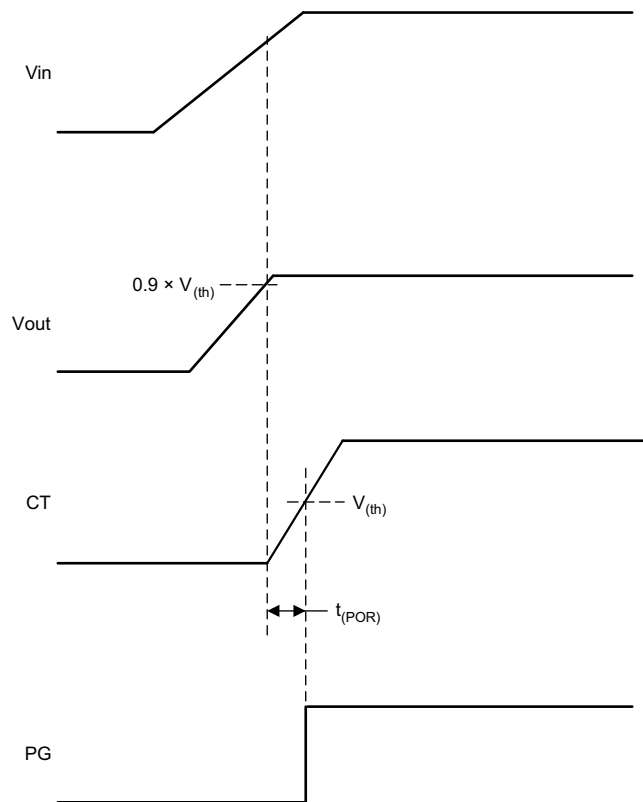


图 15. External Programmable Reset Delay

7.3.5 Undervoltage Shutdown

There is an internally fixed undervoltage shutdown threshold. Undervoltage shutdown activates when the input voltage on V_{in} drops below $V_{(inUVLO)}$. This ensures the regulator is not latched into an unknown state during low input supply voltage. If the input voltage has a negative transient which drops below the UVLO threshold and recovers, the regulator shuts down and powers up with a normal power-up sequence once the input voltage is above the required levels.

7.3.6 Low-Voltage Tracking

At low input voltages, the regulator drops out of regulation and the output voltage tracks input minus a voltage based on the load current (I_O) and switch resistance ($R_{(SW)}$). This allows for a smaller input capacitor and can possibly eliminate the need of using a boost converter during cold-crank conditions.

7.3.7 Thermal Shutdown

These devices incorporate a thermal shutdown (TSD) circuit as a protection from overheating. For continuous normal operation, the junction temperature should not exceed the TSD trip point. If the junction temperature exceeds the TSD trip point, the output turns off. When the junction temperature falls below the TSD trip point, the output turns on again.

Thermal protection disables the output when the junction temperature rises to approximately 175°C, allowing the device to cool. Cooling of the junction temperature to approximately 155°C enables the output circuitry. Depending on power dissipation, thermal resistance, and ambient temperature, the thermal protection circuit may cycle on and off. This cycling limits the dissipation of the regulator, protecting it from damage as a result of overheating.

Feature Description (接下页)

The purpose of the design of the internal protection circuitry of the TPS7A6650H-Q1 is for protection against overload conditions, not as a replacement for proper heat-sinking. Continuously running the TPS7A6650H-Q1 device into thermal shutdown degrades device reliability.

7.4 Device Functional Modes

7.4.1 Operation With $V_{(VIN)} < 4\text{ V}$

The devices operate with input voltages above 4 V. The maximum UVLO voltage is 2.6 V, and the devices operate at an input voltage above 4 V. The devices can also operate at lower input voltages; no minimum UVLO voltage is specified. At input voltages below the actual UVLO voltage, the devices do not operate.

7.4.2 Operation With EN Control

The enable rising edge threshold voltage is 1.7 V (maximum). With the EN pin held above that voltage and the input voltage above 4 V, the device becomes active. The enable falling edge is 0.4 V (minimum). Holding the EN pin below that voltage disables the device, thus reducing the IC quiescent current.

8 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The TPS7A6650H-Q1 device is a 150-mA low-dropout linear regulator designed for up to 40-V V_{in} operation with only 12- μ A quiescent current at no load.

8.2 Typical Application

图 16 shows a typical application circuits for the TPS7A6650H-Q1. One may use different values of external components, depending on the end application. An application may require a larger output capacitor during fast load steps in order to prevent reset from occurring. TI recommends a low-ESR ceramic capacitor with dielectric of type X7R or X8R.

8.2.1 TPS7A6650H-Q1 Typical Application

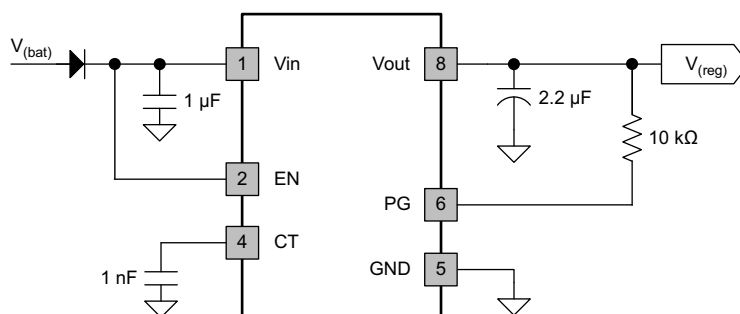


图 16. Typical Application Schematic for TPS7A6650H-Q1

8.2.1.1 Design Requirements

For this design example, use the parameters listed in 表 1 as the design parameters.

表 1. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
Input voltage range	4 V to 40 V
Output voltage	5 V
Output current rating	50 mA
Output capacitor range	2.2 μ F to 100 μ F
Output capacitor ESR range	1 m Ω to 2 Ω
CT capacitor range	100 pF to 100 nF

8.2.1.2 Detailed Design Procedure

To begin the design process, determine the following:

- Input voltage range
- Output voltage
- Output current rating
- Input capacitor
- Output capacitor
- Power-up-reset delay time

8.2.1.2.1 Input Capacitor

The device requires an input decoupling capacitor, the value of which depends on the application. The typical recommended value for the decoupling capacitor is 10 μF . The voltage rating must be greater than the maximum input voltage.

8.2.1.2.2 Output Capacitor

The device requires an output capacitor to stabilize the output voltage. The capacitor value should be between 2.2 μF and 100 μF . The ESR range should be between 1 m Ω and 2 Ω . TI recommends to selecting a ceramic capacitor with low ESR to improve the load transient response.

8.2.1.3 Application Performance Plot

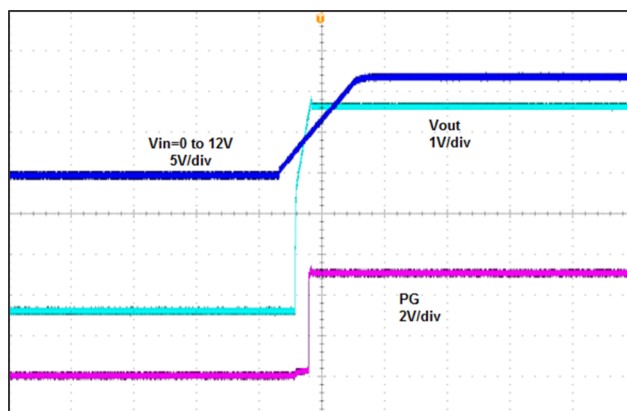


图 17. Power Up (5 V), 20 ms/div, $I_L = 20 \text{ mA}$

9 Power Supply Recommendations

Design of the device is for operation from an input voltage supply with a range between 4 V and 28 V. This input supply must be well regulated. If the input supply is located more than a few inches from the TPS7A6650H-Q1 device, TI recommends adding an electrolytic capacitor with a value of 22 μF and a ceramic bypass capacitor at the input.

10 Layout

10.1 Layout Guidelines

10.1.1 Package Mounting

Solder pad footprint recommendations for the TPS7A6650H-Q1 are available at the end of this product data sheet and at www.ti.com.

10.1.2 Board Layout Recommendations to Improve PSRR and Noise Performance

For the layout of TPS7A6650H-Q1, place the input and output capacitors close to the devices as shown in 图 18. In order to enhance the thermal performance, TI recommends surrounding the device with some vias.

To improve ac performance such as PSRR, output noise, and transient response, TI recommends a board design with separate ground planes for Vin and Vout, with each ground plane connected only at the GND pin of the device. In addition, the ground connection for the output capacitor should connect directly to the GND pin of the device.

Minimize equivalent series inductance (ESL) and ESR in order to maximize performance and ensure stability. Place every capacitor as close as possible to the device and on the same side of the PCB as the regulator itself.

Do not place any of the capacitors on the opposite side of the PCB from where the regulator is installed. TI strongly discourages the use of vias and long traces because they may impact system performance negatively and even cause instability.

If possible, and to ensure the maximum performance specified in this product data sheet, use the same layout pattern used for the TPS7A6650H-Q1 evaluation board, available at www.ti.com.

10.2 Layout Example

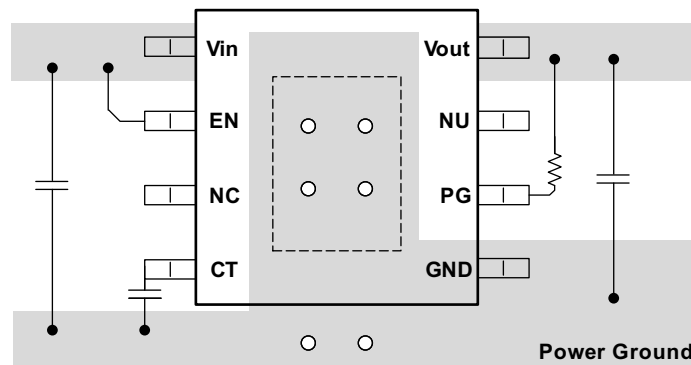


图 18. TPS7A6650H-Q1 Board Layout Diagram

10.3 Power Dissipation and Thermal Considerations

Calculate power dissipated in the device using 公式 2.

$$P_D = I_O \times (V_{(Vin)} - V_{(Vout)}) + I_{(q)} \times V_{(Vin)} \quad (2)$$

where:

P_D = continuous power dissipation

I_O = output current

$V_{(Vin)}$ = input voltage

$V_{(Vout)}$ = output voltage

As $I_{(q)} \ll I_O$, therefore ignore the term $I_{(q)} \times V_{(Vin)}$ in 公式 2.

For a device under operation at a given ambient air temperature (T_A), calculate the junction temperature (T_J) using 公式 3.

Power Dissipation and Thermal Considerations (接下页)

$$T_J = T_A + (R_{\theta JA} \times P_D) \quad (3)$$

where:

$R_{\theta JA}$ = junction-to-ambient air thermal impedance

$$\Delta T = T_J - T_A = (R_{\theta JA} \times P_D) \quad (4)$$

11 器件和文档支持

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11.3 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。本数据随时可能发生变更并且不对本文档进行修订，恕不另行通知。要获得这份数据表的浏览器版本，请查阅左侧的导航窗格。

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS7A6650HQDGNRQ1	ACTIVE	HVSSOP	DGN	8	2500	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 150	13LV	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

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(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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